

N-channel 650 V, 0.32 Ω typ., 11 A MDmesh M2 Power MOSFET in a TO-220FP package

Datasheet – production data

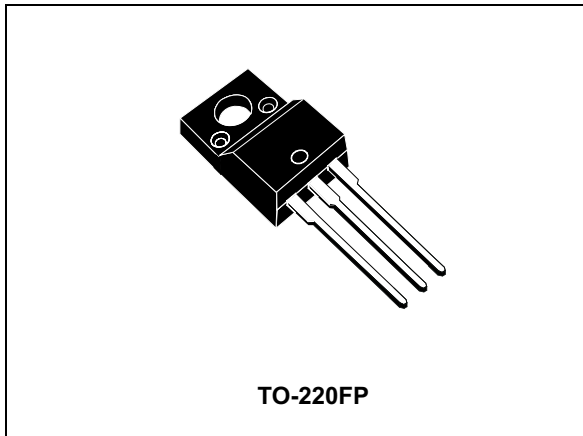
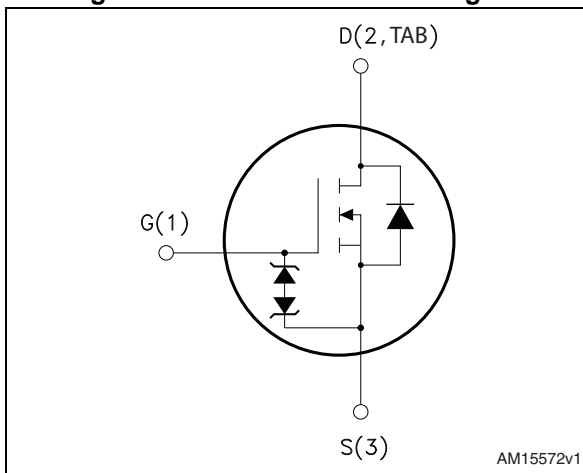


Figure 1. Internal schematic diagram



Features

| Order code | $V_{DS} @ T_{Jmax}$ | $R_{DS(on) max}$ | I_D |
|------------|---------------------|------------------|-------|
| STF16N65M2 | 710 V | 0.36 Ω | 11 A |

- Extremely low gate charge
- Excellent output capacitance (C_{oss}) profile
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1. Device summary

| Order codes | Marking | Package | Packaging |
|-------------|---------|----------|-----------|
| STF16N65M2 | 16N65M2 | TO-220FP | Tube |

Contents

| | | |
|----------|---|-----------|
| 1 | Electrical ratings | 3 |
| 2 | Electrical characteristics | 4 |
| | 2.1 Electrical characteristics (curves) | 6 |
| 3 | Test circuits | 8 |
| 4 | Package mechanical data | 9 |
| 5 | Revision history | 12 |

1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|--|-------------|------------------|
| V_{GS} | Gate-source voltage | ± 25 | V |
| $I_D^{(1)}$ | Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$ | 11 | A |
| I_D | Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$ | 6.9 | A |
| $I_{DM}^{(2)}$ | Drain current (pulsed) | 44 | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ }^\circ\text{C}$ | 25 | W |
| $dv/dt^{(3)}$ | Peak diode recovery voltage slope | 15 | V/ns |
| $dv/dt^{(4)}$ | MOSFET dv/dt ruggedness | 50 | V/ns |
| V_{ISO} | Insulation withstand voltage (RMS) from all three leads to external heat sink ($t=1\text{ s}; T_C=25\text{ }^\circ\text{C}$) | 2500 | V |
| T_{stg} | Storage temperature | - 55 to 150 | $^\circ\text{C}$ |
| T_j | Max. operating junction temperature | | |

1. Limited only by maximum temperature allowed.
2. Pulse width limited by safe operating area.
3. $I_{SD} \leq 11\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD}=400\text{ V}$.
4. $V_{DS} \leq 520\text{ V}$

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|----------------|---|-------|---------------------------|
| $R_{thj-case}$ | Thermal resistance junction-case max | 5 | $^\circ\text{C}/\text{W}$ |
| $R_{thj-amb}$ | Thermal resistance junction-ambient max | 62.50 | $^\circ\text{C}/\text{W}$ |

Table 4. Avalanche characteristics

| Symbol | Parameter | Value | Unit |
|----------|---|-------|------|
| I_{AR} | Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax}) | 1.9 | A |
| E_{AS} | Single pulse avalanche energy (starting $T_j=25\text{ }^\circ\text{C}$, $I_D=I_{AR}$; $V_{DD}=50$) | 360 | mJ |

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 5. On /off states

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|-----------------------------------|--|------|------|----------|---------------|
| $V_{(BR)DSS}$ | Drain-source breakdown voltage | $V_{GS} = 0, I_D = 1\text{ mA}$ | 650 | | | V |
| I_{DSS} | Zero gate voltage drain current | $V_{GS} = 0, V_{DS} = 650\text{ V}$ | | | 1 | μA |
| | | $V_{GS} = 0, V_{DS} = 650\text{ V}, T_C = 125\text{ °C}$ | | | 100 | μA |
| I_{GSS} | Gate-body leakage current | $V_{DS} = 0, V_{GS} = \pm 25\text{ V}$ | | | ± 10 | μA |
| $V_{GS(th)}$ | Gate threshold voltage | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$ | 2 | 3 | 4 | V |
| $R_{DS(on)}$ | Static drain-source on-resistance | $V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$ | | 0.32 | 0.36 | Ω |

Table 6. Dynamic

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|----------------------------|-------------------------------|---|------|------|------|----------|
| C_{iss} | Input capacitance | $V_{GS} = 0, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$ | - | 718 | - | pF |
| C_{oss} | Output capacitance | | - | 32 | - | pF |
| C_{riss} | Reverse transfer capacitance | | - | 1.1 | - | pF |
| $C_{oss\text{ eq.}}^{(1)}$ | Equivalent output capacitance | $V_{GS} = 0, V_{DS} = 0\text{ to }520\text{ V}$ | - | 189 | - | pF |
| R_G | Intrinsic gate resistance | $f = 1\text{ MHz open drain}$ | - | 5.2 | - | Ω |
| Q_g | Total gate charge | $V_{DD} = 520\text{ V}, I_D = 11\text{ A}, V_{GS} = 10\text{ V}$ (see Figure 15) | - | 19.5 | - | nC |
| Q_{gs} | Gate-source charge | | - | 4 | - | nC |
| Q_{gd} | Gate-drain charge | | - | 8.3 | - | nC |

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7. Switching times

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|---------------------|---|------|------|------|------|
| $t_{d(on)}$ | Turn-on delay time | $V_{DD} = 325\text{ V}$, $I_D = 5.5\text{ A}$, $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$ (see Figure 14 and 19) | - | 11.3 | - | ns |
| t_r | Rise time | | - | 8.2 | - | ns |
| $t_{d(off)}$ | Turn-off delay time | | - | 36 | - | ns |
| t_f | Fall time | | - | 11.3 | - | ns |

Table 8. Source drain diode

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|-------------------------------|---|------|------|------|---------------|
| I_{SD} | Source-drain current | | - | | 11 | A |
| $I_{SDM}^{(1)}$ | Source-drain current (pulsed) | | - | | 44 | A |
| $V_{SD}^{(2)}$ | Forward on voltage | $V_{GS} = 0$, $I_{SD} = 11\text{ A}$ | - | | 1.6 | V |
| t_{rr} | Reverse recovery time | $I_{SD} = 11\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$ (see Figure 16) | - | 342 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 3.5 | | μC |
| I_{RRM} | Reverse recovery current | | - | 20.4 | | A |
| t_{rr} | Reverse recovery time | $I_{SD} = 11\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 16) | - | 458 | | ns |
| Q_{rr} | Reverse recovery charge | | - | 4.6 | | μC |
| I_{RRM} | Reverse recovery current | | - | 20.5 | | A |

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

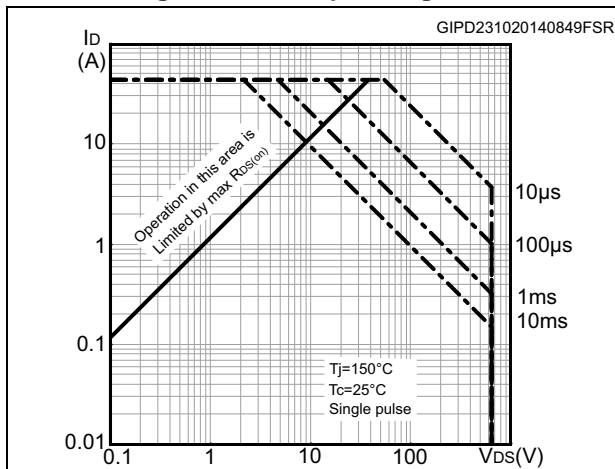


Figure 3. Thermal impedance

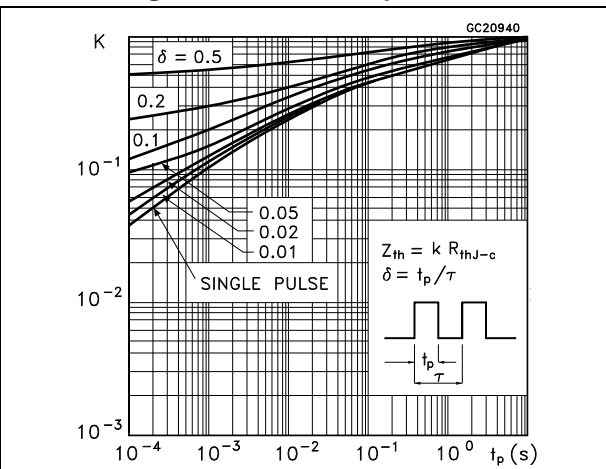


Figure 4. Output characteristics

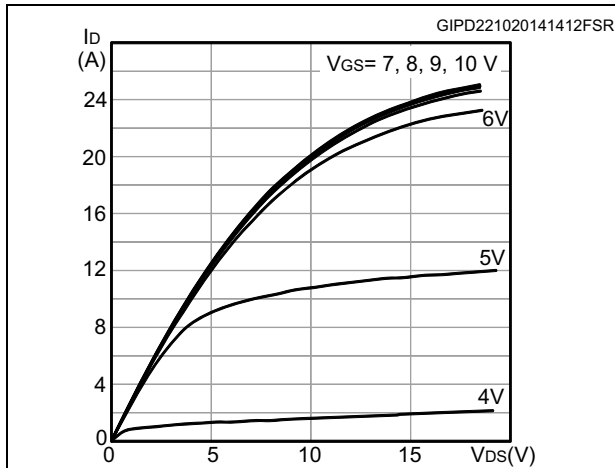


Figure 5. Transfer characteristics

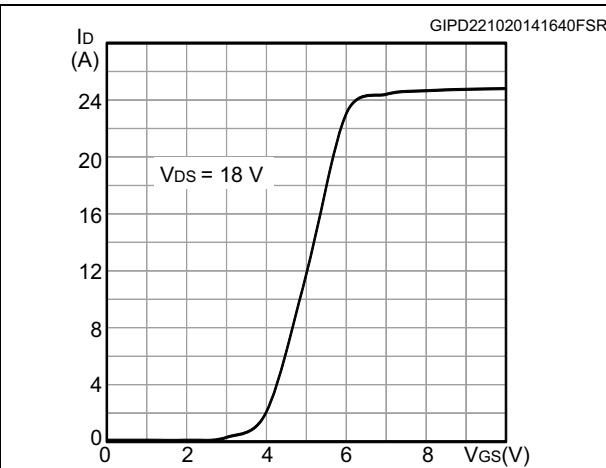


Figure 6. Normalized gate threshold voltage vs. temperature

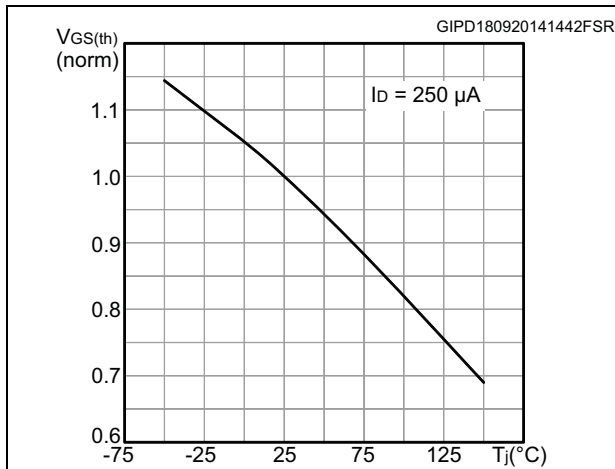


Figure 7. Normalized $V_{(BR)DSS}$ vs. temperature

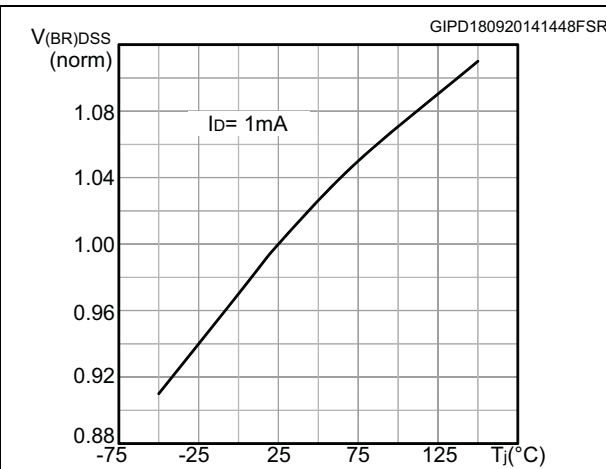


Figure 8. Static drain-source on-resistance

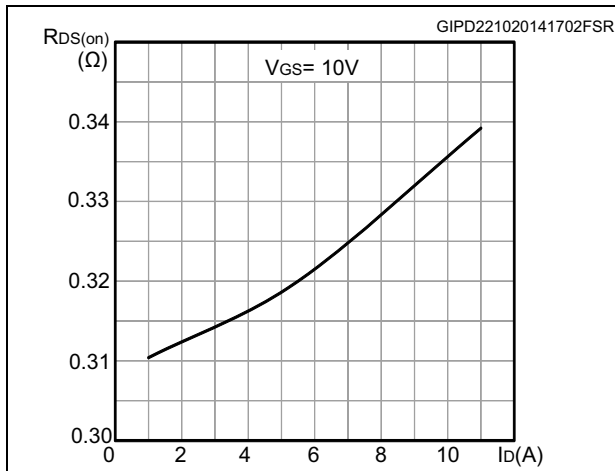


Figure 9. Normalized on-resistance vs. temperature

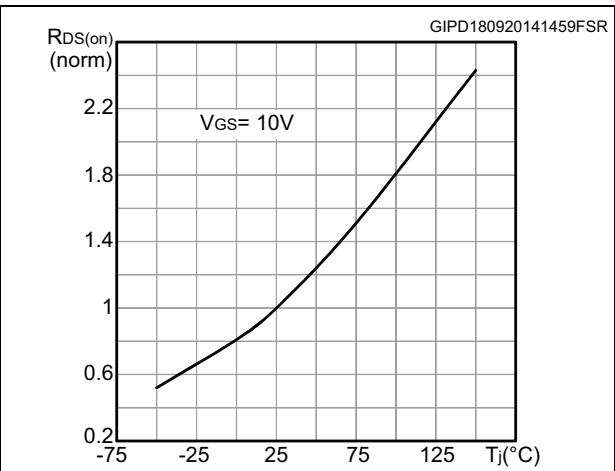


Figure 10. Gate charge vs. gate-source voltage

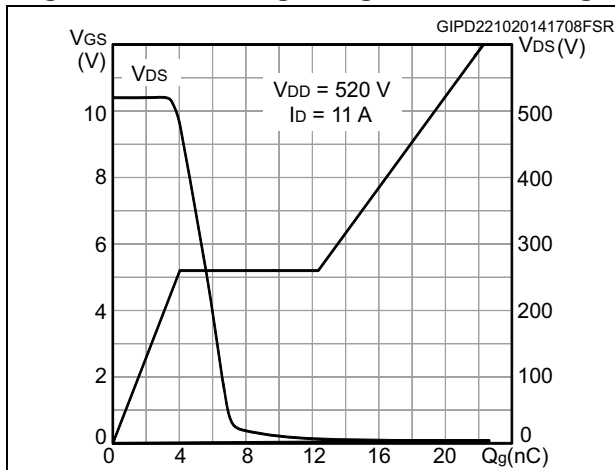


Figure 11. Capacitance variations

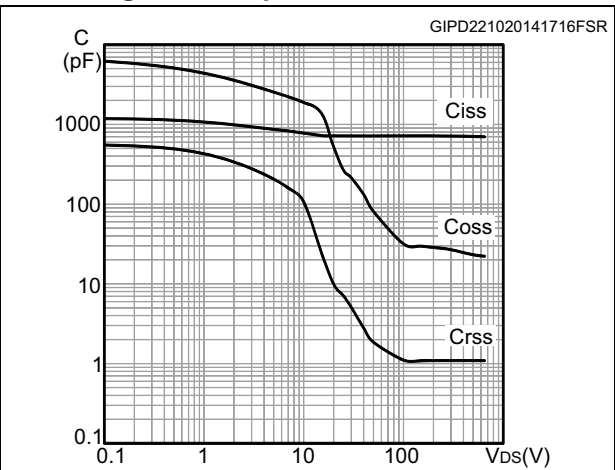


Figure 12. Output capacitance stored energy

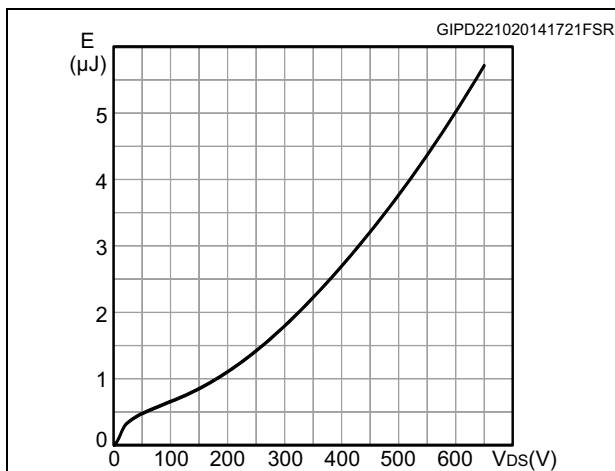
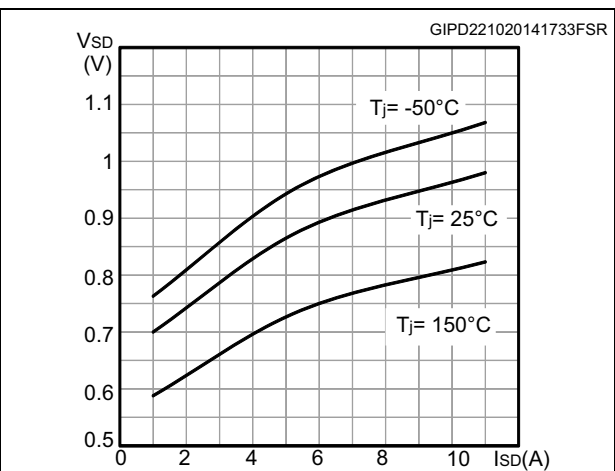
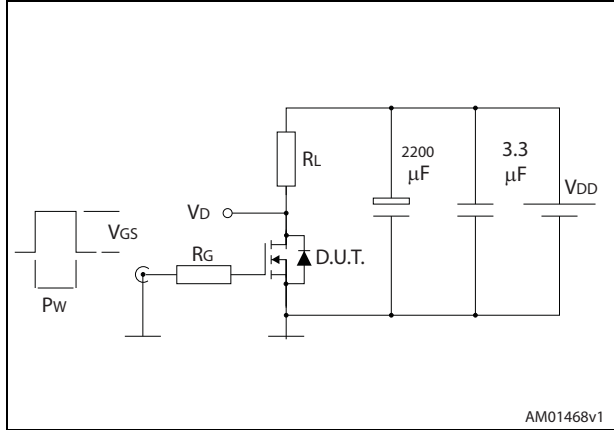


Figure 13. Source-drain diode forward characteristics



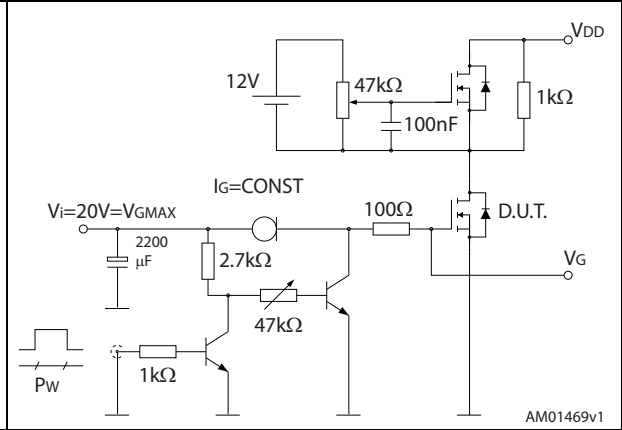
3 Test circuits

Figure 14. Switching times test circuit for resistive load



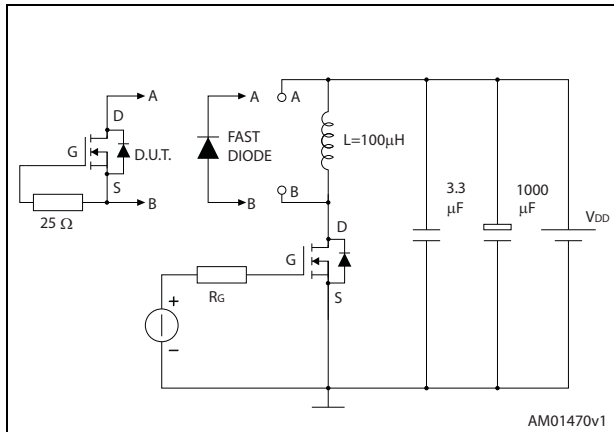
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Figure 15. Gate charge test circuit



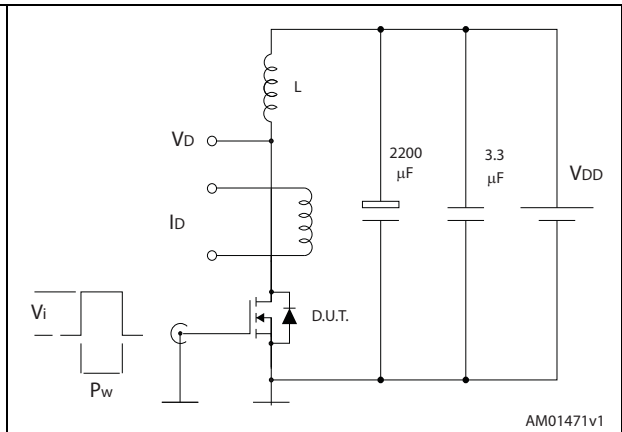
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Figure 16. Test circuit for inductive load switching and diode recovery times



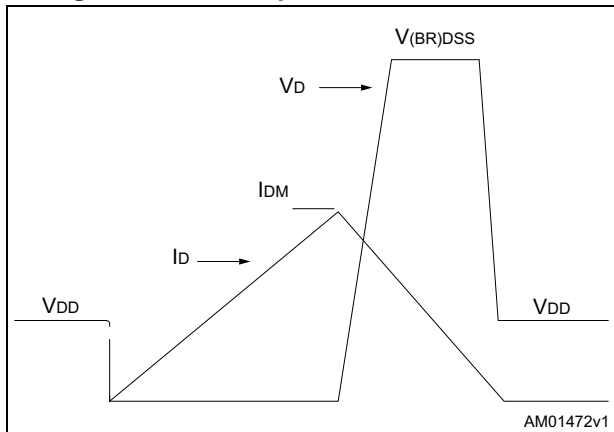
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Figure 17. Unclamped inductive load test circuit



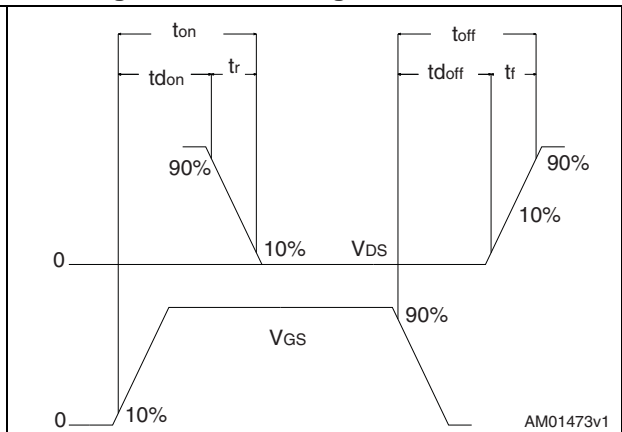
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Figure 18. Unclamped inductive waveform



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Figure 19. Switching time waveform

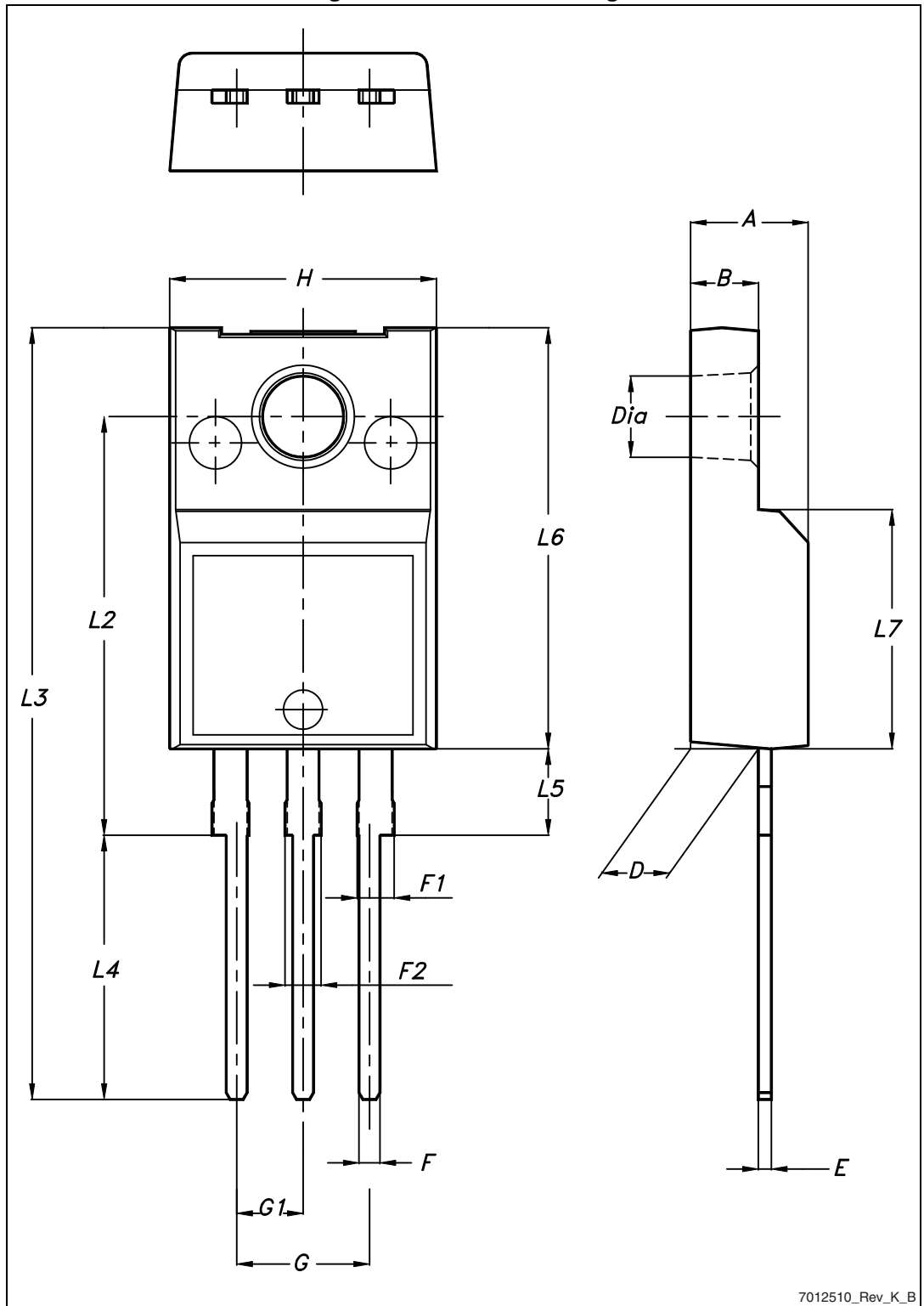


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4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Figure 20. TO-220FP drawing



7012510_Rev_K_B

Table 9. TO-220FP mechanical data

| Dim. | mm | | |
|------|------|------|------|
| | Min. | Typ. | Max. |
| A | 4.4 | | 4.6 |
| B | 2.5 | | 2.7 |
| D | 2.5 | | 2.75 |
| E | 0.45 | | 0.7 |
| F | 0.75 | | 1 |
| F1 | 1.15 | | 1.70 |
| F2 | 1.15 | | 1.70 |
| G | 4.95 | | 5.2 |
| G1 | 2.4 | | 2.7 |
| H | 10 | | 10.4 |
| L2 | | 16 | |
| L3 | 28.6 | | 30.6 |
| L4 | 9.8 | | 10.6 |
| L5 | 2.9 | | 3.6 |
| L6 | 15.9 | | 16.4 |
| L7 | 9 | | 9.3 |
| Ø | 3 | | 3.2 |

5 Revision history

Table 10. Document revision history

| Date | Revision | Changes |
|-------------|----------|----------------|
| 24-Oct-2014 | 1 | First release. |

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